

8254735 SILICONIX INC

03E 12043 D



DG126/129/140

Dual DPST JFET

Analog Switches

T-51-11

FEATURES

- < 1 mW Standby Power
- Bipolar Drivers
- Constant $r_{DS(ON)}$ Over Signal Range
- OFF Isolation > 60 dB @ 1 MHz

BENEFITS

- Minimizes Standby Power Requirements
- Better Radiation Tolerance
- Less Distortion
- Higher Frequency Switching

APPLICATIONS

- Portable and Battery Powered Systems
- Switching in Satellite Applications
- Low Distortion Circuits
- High Frequency Switching Circuits

DESCRIPTION

The DG126, DG129 and DG140 are dual double-pole single-throw analog switches for use in instrumentation, process control, and audio communication systems. This series is ideally suited for applications requiring a constant ON resistance over the entire analog range.

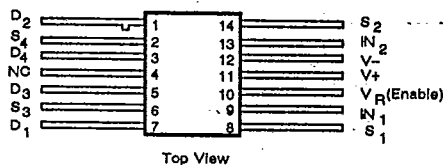
ON resistance for the DG126 is < 80 Ω , the DG129 < 30 Ω and the DG140 < 10 Ω , and ON leakage for all three is < 2 nA. With all switches OFF, total power consumption is < 750 μ W. These switches have Make-Before-Break action and due to the processing are relatively Radiation tolerant. An enable pin (V_R) simplifies interfacing with microprocessor, or other logic. Package options are the 14-pin side braze and flat pack.

Each device contains four junction-type field-effect transistors (JFETS) to achieve constant on resistance. Level-shifting drivers enable low-level inputs (0.8 to 2.5 V) to control the ON-OFF state of each switch. With logic "0" at the driver input the switches will be OFF. With a logic "1" at the input the switches will be ON. In the ON state each switch will conduct current in either direction, and in the OFF state each switch will block voltages up to 20 V peak-to-peak.

Packaging for this series includes 14-pin side braze and flatpack options. Performance grades include both military, A suffix (-55 to 125°C) and Industrial, B suffix (-25 to 85°C) temperature ranges. The flatpack option is only available in the military grade.

PIN CONFIGURATION

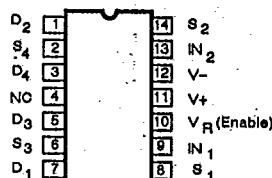
Flat Package



Top View

Order Numbers:
DG126AL/883, DG129AL/883,
DG140AL/883

Dual-In-Line Package



Top View

Order Numbers:
DG126AP, DG126BP
DG129AP, DG129BP
DG140AP, DG140BP

Not Recommended for New Designs

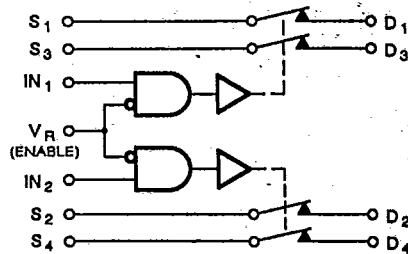
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FUNCTIONAL BLOCK DIAGRAM

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Two DPST Switches per Package*

Truth Table

LOGIC	SWITCH
0	OFF
1	ON

Logic "0" < 0.8 V

Logic "1" ≥ 2.5 V

*Switches Shown for Logic "1" Input

ABSOLUTE MAXIMUM RATINGS

V ₊ to V ₋	38 V
V ₊ to V _D	38 V
V _D or V _S to V ₋	38 V
V _D to V _S	±22 V
V ₊ to V _R	25 V
V _R to V ₋	25 V
V _{IN} to V ₋	30 V
V ₊ to V _{IN}	25 V
V _{IN} to V _R	±6 V

Current (Any Terminal)	30 mA
Storage Temperature	-65 to 150°C
Operating Temperature (A Suffix)	-55 to 125°C
(B Suffix)	-25 to 85°C

Power Dissipation*

Flat Package**	750 mW
14-pin DIP***	825 mW

* All leads welded or soldered to PC board.

** Derate 10 mW/°C above 75°C.

*** Derate 11 mW/°C above 75°C.

ELECTRICAL CHARACTERISTICS^a**DG126**

PARAMETER	SYMBOL	Test Conditions Unless Otherwise Specified: V ₊ = 12 V V ₋ = -18 V V _R = 0 V		LIMITS						UNIT
				1=25°C 2=125,85°C 3=-55,-25°C		A SUFFIX -55 to 125°C		B SUFFIX -25 to 85°C		
				TEMP	TYP ^d	MIN ^b	MAX ^b	MIN ^b	MAX ^b	
				SWITCH						
Analog Signal Range	V _{ANALOG}			1,2,3		-10	10	-8	8	V
Drain-Source ON Resistance	r _{DS(ON)}	I _S = -10 mA V _{IN} = 2.5 V	V _D = 10 V	1,3 2	30		80 150		150	Ω
			V _D = 8 V	1,3 2	25				100 150	
Source OFF Leakage Current	I _{S(OFF)}	V _{IN} = 0.8 V	V _S = 10 V V _D = -10 V	1 2	0.01		1 100			nA
			V _S = 8 V V _D = -8 V	1 2	0.05				5 100	
Drain OFF Leakage Current	I _{D(OFF)}		V _D = 10 V V _S = -10 V	1 2	0.005		1 100			
			V _D = 8 V V _S = -8 V	1 2	0.025				5 100	

Not Recommended for New Designs

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**DG126/129/140**

ELECTRICAL CHARACTERISTICS ^a											DG126
PARAMETER	SYMBOL	Test Conditions Unless Otherwise Specified: V ⁺ = 12 V V ⁻ = -18 V V _R = 0 V	LIMITS								UNIT
			1=25°C 2=125,85°C 3=-55,-25°C		A SUFFIX -55 to 125°C		B SUFFIX -25 to 85°C		T-51-11		
			TEMP	TYP ^d	MIN ^b	MAX ^b	MIN ^b	MAX ^b			
SWITCH (Cont'd)											
Channel ON Leakage Current	I _{D(ON)} + I _{S(ON)}	V _{IN} = 2.5 V	V _D = V _S = -10 V		1 2	-0.02	-2 -100				nA
			V _D = V _S = -8 V		1 2	-0.05			-5 -100		
INPUT											
Input Current with Input Voltage HIGH	I _{INH}	V _{IN} = 2.5 V		1,2 3	20		60 120		100 150		μA
Input Current with Input Voltage LOW	I _{INL}	V _{IN} = 0.8 V		1,3 2	0.004		0.1 2		4 4		
DYNAMIC											
Turn-ON Time ^e	t _{ON}	See Switching Time Test Circuit			1	0.4		0.6		1	μs
Turn-OFF Time ^e	t _{OFF}				1	1.3		1.6		2	
Source-OFF Capacitance	C _{S(OFF)}	f = 1 MHz	V _S = 0, I _D = 0		1	2.4					pF
Drain-OFF Capacitance	C _{D(OFF)}		V _D = 0, I _S = 0		1	2.4					
Channel ON Capacitance	C _{D+S(ON)}		V _D = V _S = 0		1	2.8					
Off Isolation		R _L = 75 Ω, f = 1 MHz			1	>60					dB
SUPPLY											
Positive Supply Current	I ⁺	One Channel ON V _{IN} = 2.5 V			1	2.1		3		3.3	mA
Negative Supply Current	I ⁻				1	-1.2	-1.8		-2.0		
Reference Supply Current	I _R				1	-1	-1.4		-1.5		
Positive Supply Current	I ⁺	All Channels OFF Both V _{IN} = 0 V			1	0.1		25		25	μA
Negative Supply Current	I ⁻				1	-0.5	-25		-25		
Reference Supply Current	I _R				1	-0.5	-25		-25		

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ELECTRICAL CHARACTERISTICS^a

DG129

PARAMETER	SYMBOL	Test Conditions Unless Otherwise Specified: V ₊ = 12 V V ₋ = -18 V V _R = 0 V		LIMITS						UNIT
				1=25°C 2=125, 85°C 3=-55, -25°C		A SUFFIX -55 to 125°C		B SUFFIX -25 to 85°C		
				TEMP	TYP ^d	MIN ^b	MAX ^b	MIN ^b	MAX ^b	
				T-51-11						

SWITCH

Analog Signal Range	V _{ANALOG}			1,2,3		-10	10	-8	8	V
Drain-Source ON Resistance	r _{DS(ON)}	I _S = -10 mA V _{IN} = 2.5 V	V _D = 10 V	1,3 2	20		30 60			Ω
			V _D = 8 V	1,3 2	30				50 75	
Source OFF Leakage Current	I _{S(OFF)}	V _{IN} = 0.8 V	V _S = 10 V V _D = -10 V	1 2	0.03		1 100			nA
			V _S = 8 V V _D = -8 V	1 2					5 100	
Drain OFF Leakage Current	I _{D(OFF)}		V _D = 10 V V _S = -10 V	1 2	0.02		1 100			
			V _D = 8 V V _S = -8 V	1 2	0.1				5 100	
Channel ON Leakage Current	I _{D(ON)} + I _{S(ON)}	V _{IN} = 2.5 V	V _D = V _S = -10 V	1 2	-0.03	-2 -100				
			V _D = V _S = -8 V	1 2	-0.08			-5 -100		

INPUT

Input Current with Input Voltage HIGH	I _{INH}	V _{IN} = 2.5 V		1,2 3	15		60 120		100 150	μA
Input Current with Input Voltage LOW	I _{INL}	V _{IN} = 0.8 V		1,3 2	0.005		0.1 2		4 4	

DYNAMIC

Turn-ON Time ^e	t _{ON}	See Switching Time Test Circuit		1	0.5		0.6		1	μs
Turn-OFF Time ^e	t _{OFF}			1	1.1		1.6		2	
Source-OFF Capacitance	C _{S(OFF)}	f = 1 MHz	V _S = 0, I _D = 0	1	2.4					pF
Drain-OFF Capacitance	C _{D(OFF)}		V _D = 0, I _S = 0	1	2.4					
Channel ON Capacitance	C _{D+S(ON)}		V _D = V _S = 0	1	2.8					
Off Isolation		R _L = 75 Ω, f = 1 MHz		1	>60					dB

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DG126/129/140



ELECTRICAL CHARACTERISTICS ^a										DG140
PARAMETER	SYMBOL	Test Conditions Unless Otherwise Specified: V ₊ = 12 V V ₋ = -18 V V _R = 0 V	LIMITS						UNIT	T-51-11
			1=25°C 2=125, 85°C 3=-55, -25°C		A SUFFIX -55 to 125°C		B SUFFIX -25 to 85°C			
			TEMP	TYP ^d	MIN ^b	MAX ^b	MIN ^b	MAX ^b		
INPUT										
Input Current with Input Voltage HIGH	I _{INH}	V _{IN} = 2.5 V	1, 2 3	13		60 120		100 150		μA
Input Current with Input Voltage LOW	I _{INL}	V _{IN} = 0.8 V	1, 3 2	0.004		0.1 2		4 4		μA
DYNAMIC										
Turn-ON Time ^e	t _{ON}	See Switching Time Test Circuit		1	0.6		1		1.5	μs
Turn-OFF Time ^e	t _{OFF}			1	1.15		2.5		2.5	μs
Source-OFF Capacitance	C _{S(OFF)}	f = 1 MHz	V _S = 0, I _D = 0		1	3				pF
Drain-OFF Capacitance	C _{D(OFF)}		V _D = 0, I _S = 0		1	3				
Channel ON Capacitance	C _{D+S(ON)}		V _D = V _S = 0		1	2.8				
Off Isolation		R _L = 75 Ω, f = 1 MHz		1	>50					dB
SUPPLY										
Positive Supply Current	I ₊	One Channel ON V _{IN} = 2.5 V		1	2.4		3		3.3	mA
Negative Supply Current	I ₋			1	-1.5	-1.8		-2.0		
Reference Supply Current	I _R			1	-1	-1.4		-1.5		
Positive Supply Current	I ₊	All Channels OFF Both V _{IN} = 0 V		1	0.1		25		25	μA
Negative Supply Current	I ₋			1	-0.5	-25		-25		
Reference Supply Current	I _R			1	-0.5	-25		-25		

NOTES:

- a. Refer to PROCESS OPTION FLOWCHART for additional information.
 b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
 c. Guaranteed by design, not subject to production test.
 d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
 e. V_{IN} must be a step function with a minimum rise and fall time of 1 V/ μs .

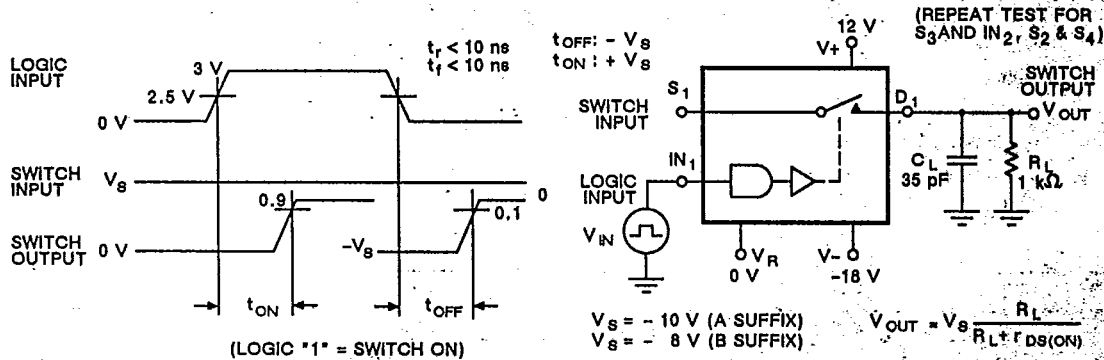
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**DG126/129/140****SWITCHING TIME TEST CIRCUIT**

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Switch output waveform shown for V_S = constant with logic input waveform as shown. Note that V_S may be + or - as per switching time test circuit. V_O is the steady state output with switch on. Feedthrough via gate capacitance may result in spikes at leading and trailing edge of output waveform.



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APPLICATION HINTS

V+ Positive Supply Voltage (V)	V- Negative Supply Voltage (V)	V _R Reference Voltage (V)	V _{IN} Logic Input Voltage V _{INH} Min/ V _{INL} Max (V)	V _S or V _D Analog Voltage Range (V)
12	-18	0	2.5/0.8	-10 to 10
15	-15	0	2.5/0.8	-7 to 13
7	-12	0	2.5/0.8	-5 to 5
5	-15	0	2.5/0.8	-7 to 3
5	-10	0	2.5/0.8	-2 to 3

Not Recommended for New Designs

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